

Bipolar Transistor

(-)100 V, (-)1 A, Low V_{CE}(sat), (PNP)NPN Single PCP

2SA1416, 2SC3646

Features

- Adoption of FBET and MBIT Processes
- High Breakdown Voltage and Large Current Capacity
- Fast Switching Speed
- Ultrasmall Size Making it Easy to Provide High-Density Small-Sized Hybrid IC's
- These Devices are Pb-Free and are RoHS Compliant

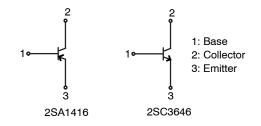
SPECIFICATIONS (): 2SA1416 ABSOLUTE MAXIMUM RATINGS at Ta = 25°C

Parameter	Symbol	Value	Unit
Collector to Base Voltage	V _{CBO}	(-) 120	V
Collector to Emitter Voltage	V _{CEO}	(-) 100	V
Emitter to Base Voltage	V _{EBO}	(-) 6	V
Collector Current	Ic	(-) 1	Α
Collector Current (Pulse)	I _{CP}	(-) 2	Α
Collector Dissipation	P _C	500	mW
Collector Dissipation (Note 1)		1.3	W
Junction Temperature	T _J	150	∘C
Storage Temperature	T _{STG}	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on ceramic substrate (250 mm² x 0.8 mm).

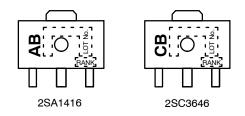
ELECTRICAL CONNECTION





SOT-89 / PCP-1 CASE 419AU

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}C$

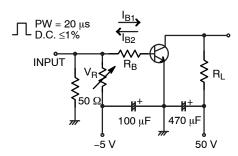
			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = (-)100 V, I _E = 0 A			(-)100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} = (-)4V, I _C = 0 A			(-)100	nA
DC Current Gain	h _{FE}	V _{CE} = (-)5 V, I _C = (-)100 mA	V _{CE} = (-)5 V, _C = (-)100 mA		400*	
Gain-Bandwidth Product	f _T	V _{CE} = (-)10 V, I _C = (-)100 mA		120		MHz
Output Capacitance	Cob	V _{CB} = (-)10 V, f = 1 MHz		(13)8.5		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)	I _C = (-)400 mA, I _B = (-)40 mA		(-0.2)0.1	(-0.6)0.4	V
Base to Emitter Saturation Voltage	V _{BE} (sat)	I _C = (-)400 mA, I _B = (-)-40 mA		(-)0.85	(-)1.2	V
Collector to Base Breakdown Voltage	V _{(BR)CBO}	$I_C = (-)10 \mu A, I_E = 0 A$	(-)120			V
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	I_C = (-)1 mA, R_{BE} = ∞	(-)100			V
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	$I_E = (-)10 \mu A, I_C = 0 A$	(-)6			V
Turn-On Time	t _{on}	See specified		(80)80		ns
Storage Time	t _{stg}	Test Circuit		(700)850		ns
Fall Time	t _f] [(40)50		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*The 2SA1416/2SC3646 are classified by 100 mA h_{FE} as follows:

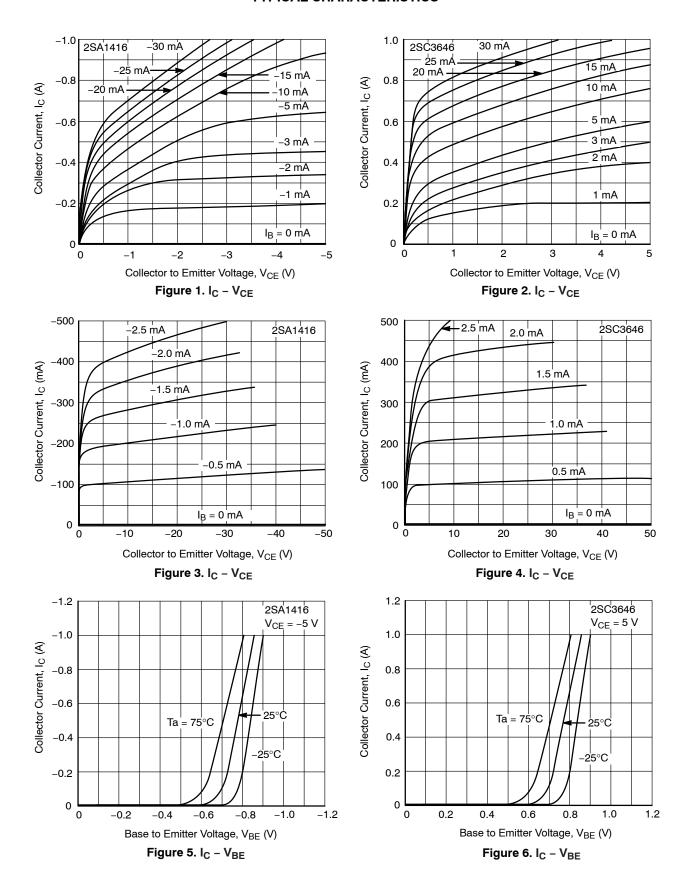
Rank	R	S	Т	
h _{FE}	100 to 200	140 to 280	200 to 400	

Switching Time Test Circuit

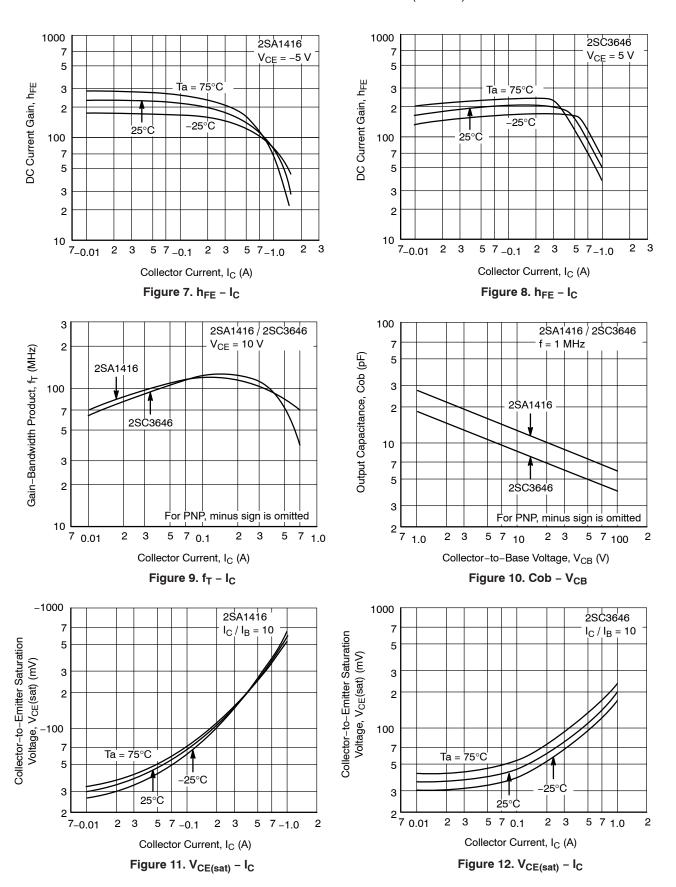


 $I_C = 10 I_{B1} = -10 I_{B2} = 400 \text{ mA}$ (For PNP, the polarity is reversed)

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (continued)



TYPICAL CHARACTERISTICS (continued)

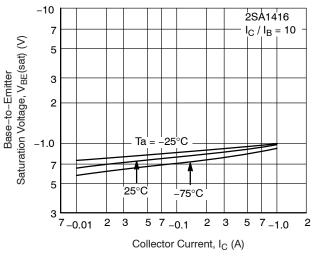


Figure 13. V_{BE}(sat) - I_C

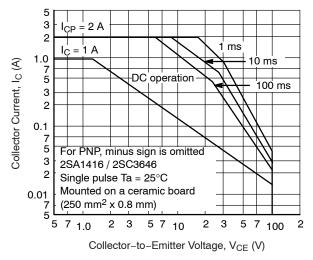


Figure 15. ASO

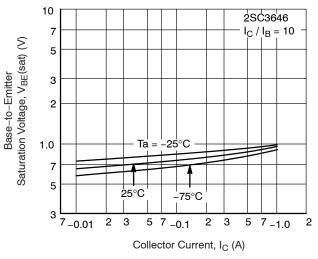


Figure 14. V_{BE}(sat) - I_C

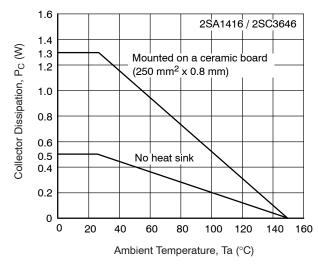


Figure 16. P_C – Ta

ORDERING INFORMATION

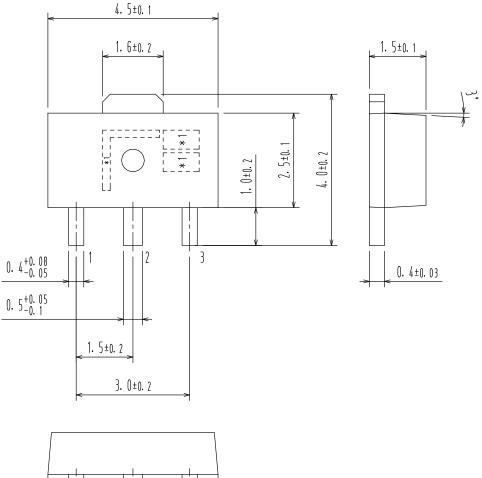
Device	Marking	Package	Shipping [†]
2SA1416S-TD-E	AB	SOT-89 / PCP-1 (Pb-Free)	1000 / Tape & Reel
2SA1416T-TD-E		(1.5.1100)	
2SC3646S-TD-E	СВ		
2SC3646T-TD-E			

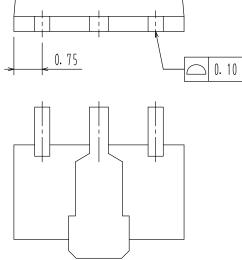
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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DATE 30 APR 2012





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